

AMENDMENTS TO THE SPECIFICATION:

Please amend the specification as follows:

Please cancel the insert following Paragraph [0058] presented with Applicant's Amendment of June 15, 2006:

~~Figure 5 illustrates another device precursor broadly designated at 25' following the annealing step of the invention previously described herein. The precursor 25' includes the silicon carbide substrate 15 and the n-type GaN layer 16. Figure 5 also illustrates a plurality of portions of silicon dioxide layer 12 on a p-type Group III nitride layer 11. As also illustrated in Figure 5, device 25' further includes a respective portion of the source composition 13 on each of the silicon dioxide portions. Figure 5 further illustrates portions of the second silicon dioxide layer 14 covering the source composition portions 13 and portions of the p-type Group III nitride layer 11. Figure 6 illustrates an alternative embodiment of the device precursor of the invention designated broadly at 25" also following the annealing step of the invention in which second silicon dioxide layer 14 is limited to portions of source composition layer 13.~~

Please inset the following after Paragraph [0058]:

Figure 5 illustrates another device precursor broadly designated at 25' following the annealing step of the invention previously described herein. The precursor 25' includes the silicon carbide substrate 15 and the n-type GaN layer 16. Figure 5 also illustrates a plurality of portions of silicon dioxide layer 12 on a p-type Group III nitride layer 11. As also illustrated in Figure 5, device 25' further includes a respective portion of the source composition 13 on each of the silicon dioxide portions 12. Figure 5 further illustrates an embodiment of the invention in which second silicon dioxide layer 14 is limited to portions of source composition layer 13. Figure 6 illustrates an alternative embodiment of the device precursor of the invention designated broadly at 25" also following the annealing step of the

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invention in which second silicon dioxide layer 14 covers the source composition portions 13 and portions of the p-type Group III nitride layer 11.